



1200V/2A Silicon Carbide Power Schottky Barrier Diode

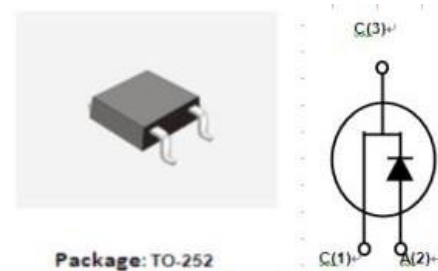
Features

- Rated to 1200V at 2 Amps
- Zero reverse recovery current
- Zero forward recovery voltage
- Temperature independent switching behaviour
- High temperature operation
- High frequency operation

Key Characteristics		
V_{RRM}	1200	V
$I_F, T_c \leq 155^\circ\text{C}$	2	A
Q_c	12	nC

Benefits

- Unipolar rectifier
- Substantially reduced switching losses
- No thermal run-away with parallel devices
- Reduced heat sink requirements



Applications

- SMPS, e.g., CCM PFC;
- Motor drives, Solar application, UPS, Wind turbine, Rail traction, EV/HEV



Part No.	Package Type	Marking
G3S12002C	TO-252	G3S12002C

Maximum Ratings

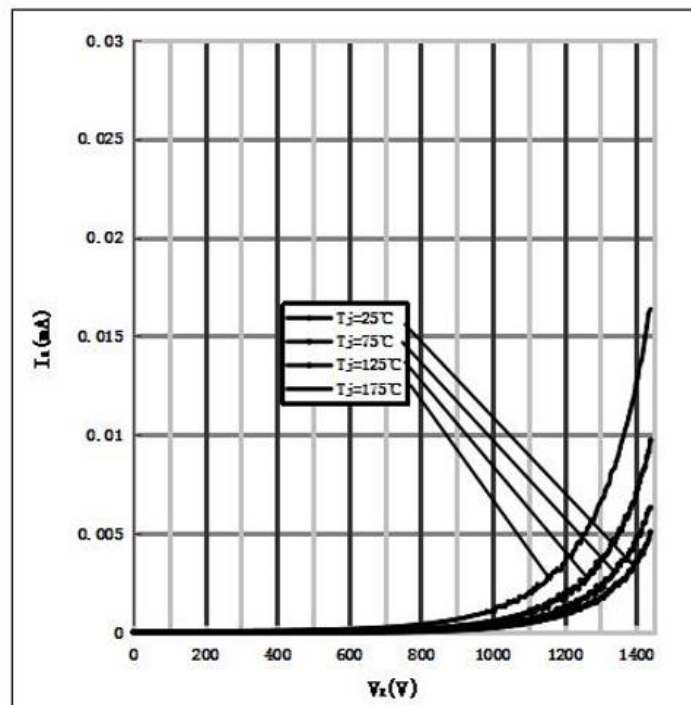
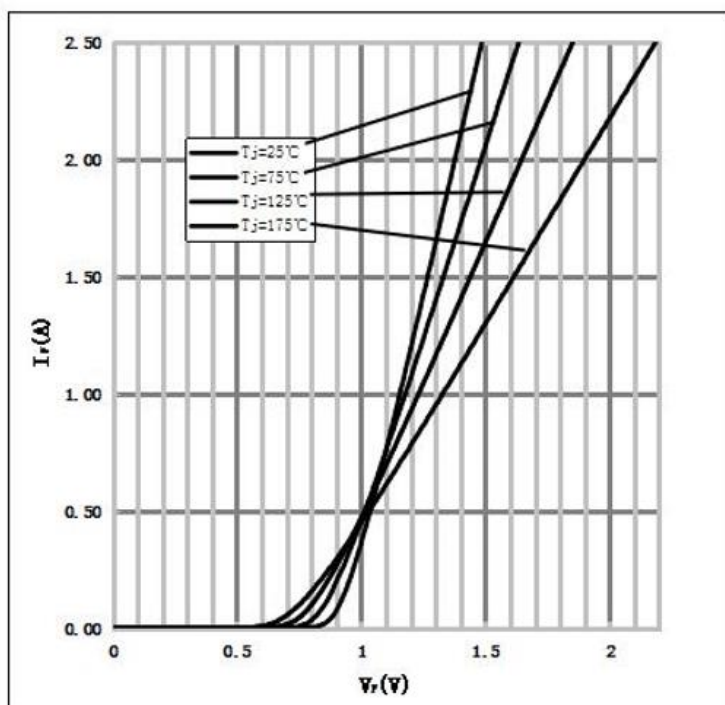
Parameter	Symbol	Test Condition	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}		1200	V
Surge Peak Reverse Voltage	V_{RSM}		1200	V
DC Blocking Voltage	V_{DC}		1200	V
Continuous Forward Current	I_F	$T_C=25^{\circ}C$ $T_C=75^{\circ}C$ $T_C=160^{\circ}C$	8.8 4.8 2	A
Repetitive Peak Forward Surge Current	I_{FRM}	$T_C=25^{\circ}C$, tp=10ms, Half Sine Wave, D=0.3	10	A
Non-repetitive Peak Forward Surge Current	I_{FSM}	$T_C=25^{\circ}C$, tp=10ms, Half Sine Wave	35	A
Power Dissipation	P_{TOT}	$T_C=25^{\circ}C$	51	W
		$T_C=110^{\circ}C$	22	W
Operating Junction	T_j		-55°C to 175°C	°C
Storage Temperature	T_{stg}		-55°C to 175°C	°C
Mounting Torque		M3 Screw	1	Nm
		6-32 Screw	8.8	lbf-in

Thermal Characteristics

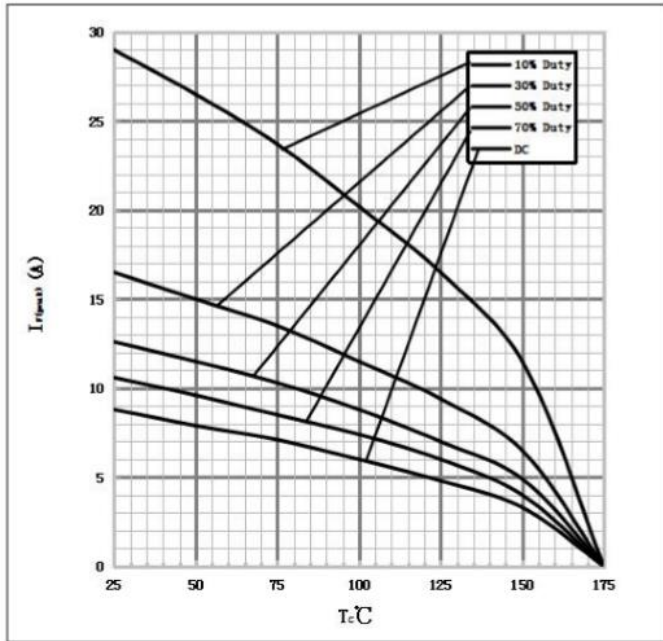
Parameter	Symbol	Test Condition	Value	Unit
			Typ.	
Thermal resistance from junction to case	$R_{th JC}$		296q7	°C/W
			qq	

Electrical Characteristics

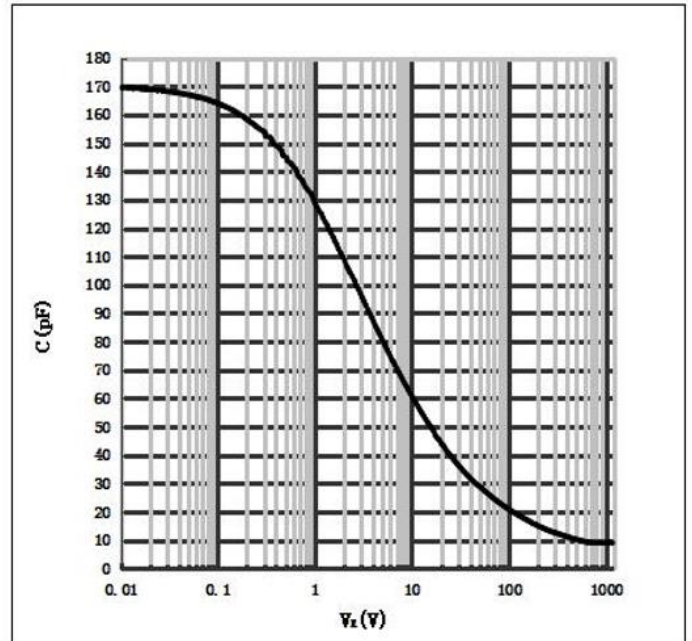
Parameter	Symbol	Test Conditions	Numerical		Unit
			Typ.	Max.	
Forward Voltage	V_F	$I_F=2A, T_j=25^\circ C$	1.38	1.7	V
		$I_F=2A, T_j=175^\circ C$	1.9	2.5	
Reverse Current	I_R	$V_R=1200V, T_j=25^\circ C$	10	50	μA
		$V_R=1200V, T_j=175^\circ C$	20	100	
Total Capacitive Charge	Q_C	$V_R=800V, T_j=150^\circ C$ $Q_C = \int_0^{V_R} C(V)dV$	12	-	nC
Total Capacitance	C	$V_R=0V, T_j=25^\circ C, f=1MHZ$	170	172	pF
		$V_R=400V, T_j=25^\circ C, f=1MHZ$	11.1	11.5	
		$V_R=800V, T_j=25^\circ C, f=1MHZ$	9.2	9.5	

Performance Graphs1) Forward IV characteristics as a function of T_j :2) Reverse IV characteristics as a function of T_j :

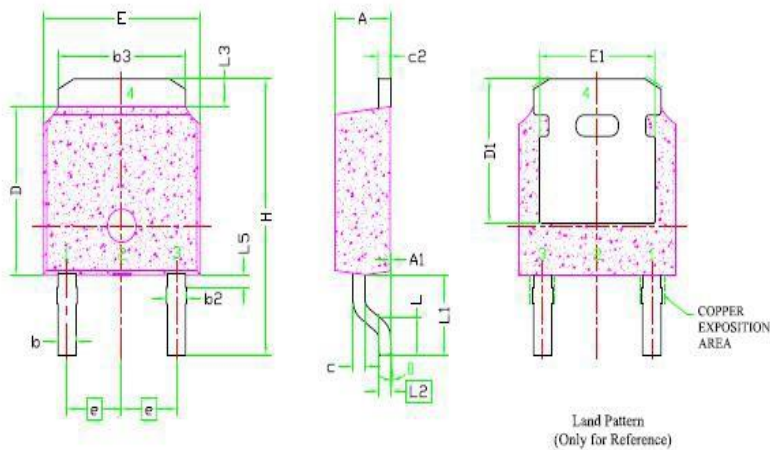
3) Current Derating



4) Capacitance vs. reverse voltage:



Package TO-252



DIM	Millimeters		
	Min.	NOM	Max.
E	6.400	6.600	6.731
L	1.400	1.520	1.770
L1	2.743 REF		
L2	0.508 BSC		
L3	0.890	-	1.270
L5	-	-	-
D	6.000	6.100	6.223
H	9.400	10.000	10.400
b	0.640	0.760	0.880
b2	0.770	0.840	1.14
b3	5.210	5.340	5.46
e	2.286 BSC		
A	2.200	2.300	2.38
A1	0.000	-	0.127
c	0.460	0.500	0.6
c2	0.460	0.500	0.58
D1	5.210	-	-
E1	4.400	-	-
θ	0°	-	10°

Note: The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC(RoHS2). RoHS Certification and other certifications can be obtained from GPT sales representatives or GPT website: <http://globalpowertech.cn/English/index.asp>

More product datasheets and company information can be found in:

<http://globalpowertech.cn/English/index.asp>

